

Features

- Ultra Low Forward Voltage Drop
- Superior Reverse Avalanche Capability
- Patented Super Barrier Rectifier Technology
- Soft, Fast Switching Capability
- 150°C Operating Junction Temperature
- **Lead Free Finish, RoHS Compliant (Note 1)**
- **“Green” Molding Compound (No Br, Sb)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: DFN1006-2
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: Cathode Dot
- Terminals: Finish - NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.001 grams



Top View



Bottom View

Maximum Ratings @T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitance load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	20	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _{RM}		
RMS Reverse Voltage	V _{R(RMS)}	14	V
Average Rectified Output Current (See Figure 1)	I _O	500	mA
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I _{FSM}	5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 2)	V _{(BR)R}	20	-	-	V	I _R = 50µA
Forward Voltage Drop	V _F	-	0.34	0.38	V	I _F = 0.1A, T _J = 25°C
			0.25	0.28		I _F = 0.1A, T _J = 150°C
			0.39	0.43		I _F = 0.2A, T _J = 25°C
			0.31	0.34		I _F = 0.2A, T _J = 150°C
			0.47	0.50		I _F = 0.5A, T _J = 25°C
			0.43	0.46		I _F = 0.5A, T _J = 150°C
Leakage Current (Note 2)	I _R	-	6	50	µA	V _R = 20V, T _J = 25°C
			1.5	5		mA

Notes: 1. RoHS revision 13.2.2003. High temperature solder exemption applied, see EU Directive Annex Note 7.
2. Short duration pulse test used to minimize self-heating effect.

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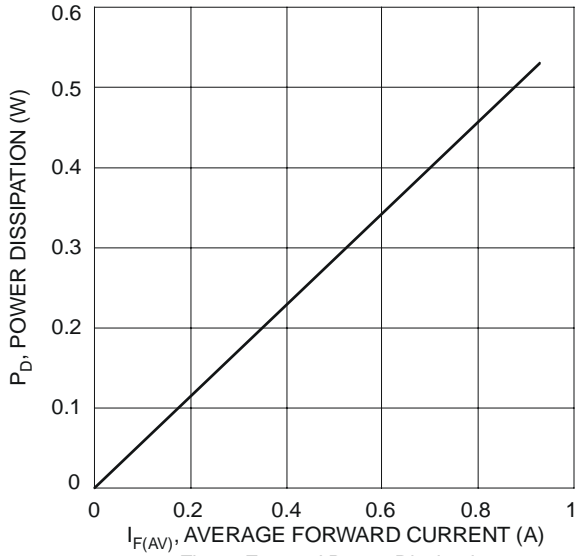


Fig. 1 Forward Power Dissipation

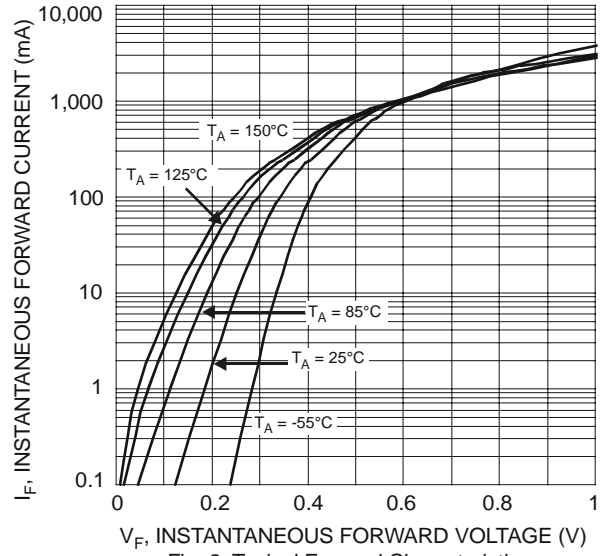


Fig. 2 Typical Forward Characteristics

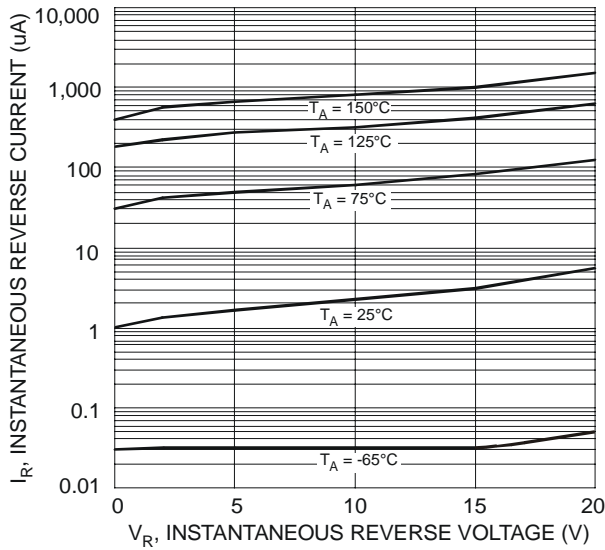


Fig. 3 Typical Reverse Characteristics

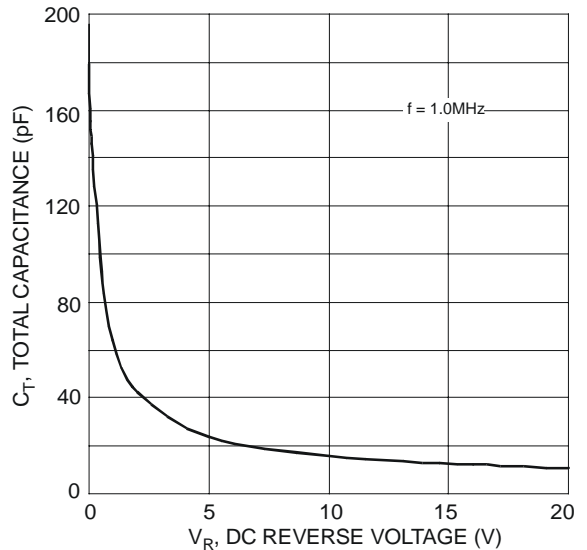


Fig. 4 Total Capacitance vs. Reverse Voltage

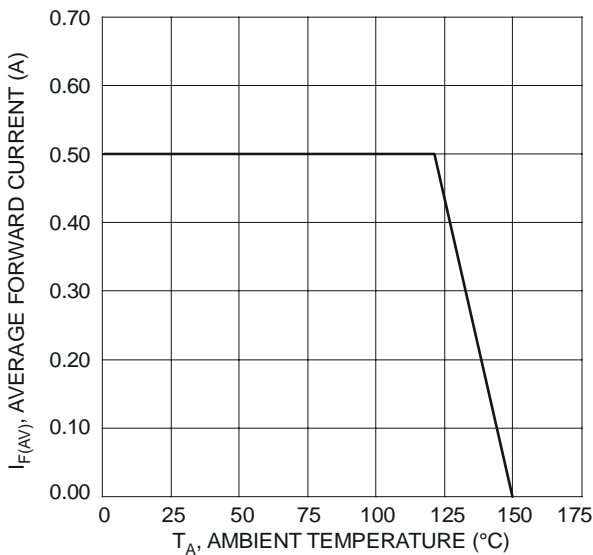


Fig. 5 Forward Current Derating Curve

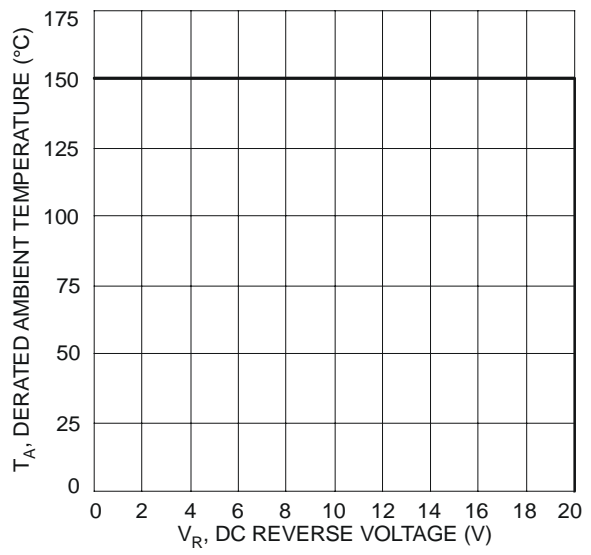


Fig. 6 Operating Temperature Derating

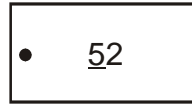
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Ordering Information (Note 3)

Part Number	Case	Packaging
SBR05U20LP-7	DFN1006-2	3000/Tape & Reel

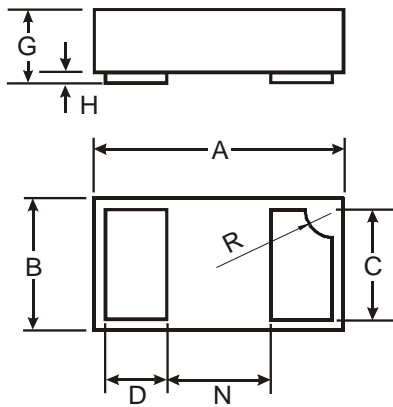
Notes: 3. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



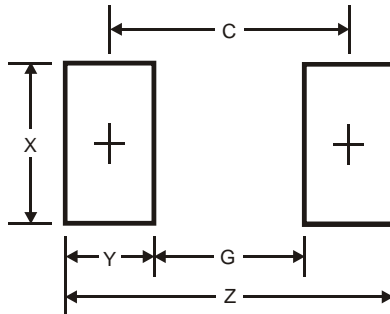
52 = Product Type Marking Code
Dot Denotes Cathode Side

Package Outline Dimensions



DFN1006-2			
Dim	Min	Max	Typ
A	0.95	1.075	1.00
B	0.55	0.675	0.60
C	0.45	0.55	0.50
D	0.20	0.30	0.25
G	0.47	0.53	0.50
H	0	0.05	0.03
N	—	—	0.40
R	0.05	0.15	0.10
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G	0.3
X	0.7
Y	0.4
C	0.7

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